Marubeni

SPECIFICATION OF LED CHIP

C830-40P

[INFRARED]

1) Commodity Type and Physical Characteristics.

1. Material		GaAlAs/GaAlAs (DDH)	
2. Electrode	Top Side	N (cathode) side	: Au Alloy & Pad
	Bottom Side	P (anode) side	: Au Alloy
3. Electrode Pattern			Fig.1
4. Chip Size			Fig.2
5. Chip Thickness			Fig.2
6. Emission Area			Fig.2

2) Electro-Optical Characteristics [Ta=25°C]

Parameters	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=20mA		1.40	1.60	V
Reverse Current	Ir	Vr=5V			10	uA
Power Intensity	Po	If=20mA	2.5	4.0		mW
Peak Wavelength	λP	If=20mA	815	830	845	nm
Spectral Radiation Bandwidth	Δλ	If=20mA		35		nm
Rise Time	tr	If=20mA		80		ns
Full time	tf	If=20mA		80		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: um]

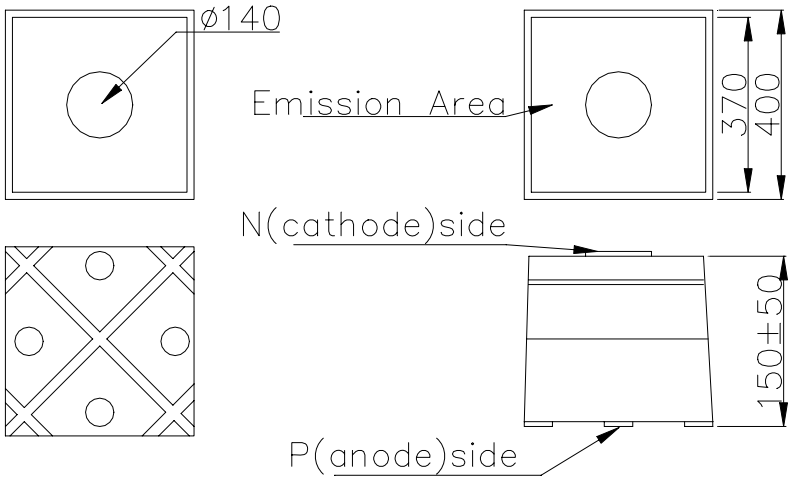

Fig.1 Electrode Pattern Fig.2 Chip size and Emission Area

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